

IN THE SPECIFICATION

Please replace Paragraph [0022] with the following amended paragraphs:

FIG. 1 is a partial sectional view of a semiconductor device, including a passivation layer, at the start of a method according to the present invention;

FIG. 2 is a partial sectional view of the semiconductor device after an entire thickness of the passivation layer over a metal line has been removed;

FIG. 3 is a partial sectional view of the semiconductor device prior to a FIB treatment step intended to remove the passivation layer over another metal line;

FIG. 4 is a partial sectional view of the semiconductor device after the entire thickness of the passivation layer has been removed over and between the metal lines;

FIG. 5 is a partial sectional view of the semiconductor device illustrating a metal bridge interconnecting the exposed metal lines; and

FIG. 6 is a partial sectional view of the semiconductor device illustrating a break in the metal bridge, the break thereby producing two contacts electrically isolated from each other.